

N-channel TrenchMOS logic level FET 13 March 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. C	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	39	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	158	W
Static chara	acteristics					
R _{DSon} drain-source o resistance	drain-source on-state	V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	43	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	29	39	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11; Fig. 12	-	34	40	mΩ
Dynamic ch	naracteristics					
Q _{GD}	gate-drain charge	V_{GS} = 5 V; I _D = 25 A; V _{DS} = 80 V; T _j = 25 °C; <u>Fig. 13</u>	-	20	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 39 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	182	mJ

Pinning information 5.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain[1]		
3	S	source		G-UFA
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

[1] It is not possible to make a connection to pin 2.

Ordering information 6.

Table 3. **Ordering information** Type number Package Name Description Version BUK9640-100A D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

Marking 7.

Table 4. Marking codes	
Type number	Marking code
BUK9640-100A	BUK9640-100A

Limiting values 8.

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage			-15	15	V
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Symbol	Parameter	Conditions	Min	Мах	Unit
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	158	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2; Fig. 3</u>	-	39	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	28	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3	-	159	А
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-dra	in diode		I		
I _S	source current	T _{mb} = 25 °C	-	39	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$	-	159	А
Avalanche	ruggedness		1		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ I_D = 39 \text{ A}; V_{sup} \le 100 \text{ V}; \text{ R}_{GS} = 50 \Omega; $	-	182	mJ

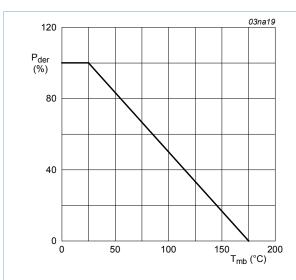


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

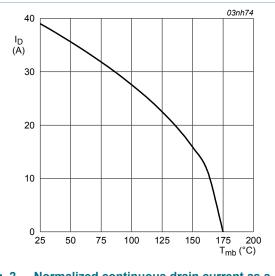


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

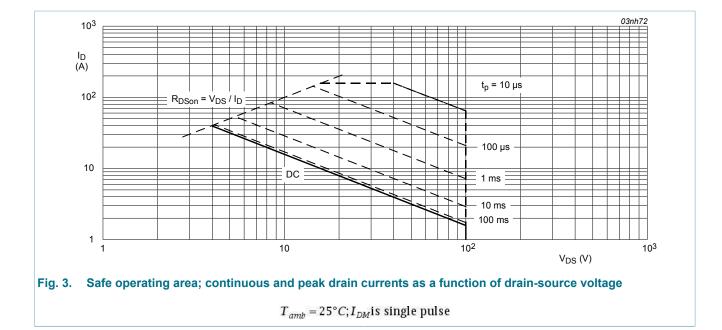
 $T_{amb} = 25^{\circ}C; I_{DM}$ is single pulse

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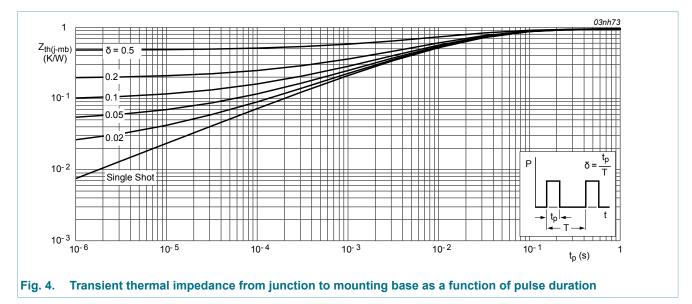
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9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>4</u>		-	-	0.95	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint		-	50	-	K/W



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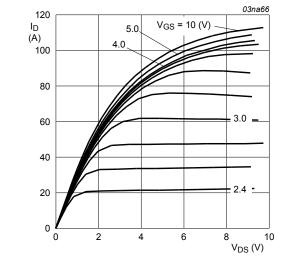
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics	· · · · ·				
V _{(BR)DSS} drain-source		I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10	1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	2.3	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	43	mΩ
resistance		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	100	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	29	39	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11; Fig. 12	-	34	40	mΩ
Dynamic ch	naracteristics	· · · · · ·	'			
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 80 V; V_{GS} = 5 V;	-	48	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u>	-	5.4	-	nC
Q _{GD}	gate-drain charge		-	20	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	2304	3072	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	222	266	pF
C _{rss}	reverse transfer capacitance		-	151	207	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω ; V _{GS} = 5 V;	-	20	-	ns
t _r	rise time	R _{G(ext)} = 10 Ω; T _j = 25 °C	-	135	-	ns
t _{d(off)}	turn-off delay time		-	125	-	ns
t _f	fall time		-	90	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_i = 25 \degree C$	-	2.5	-	nH

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		from drain lead 6 mm from package to centre of die; T_j = 25 °C	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 \ ^{\circ}C$	-	7.5	-	nH
Source-drai	in diode	·				
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 37 A; dI _S /dt = -100 A/μs;	-	60	-	ns
Qr	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C	-	240	-	nC





 $T_j = 25^{\circ}C; t_p = 300 \mu s$

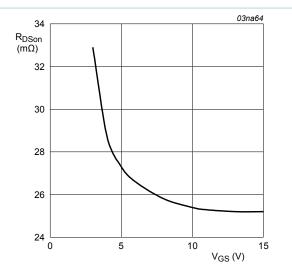
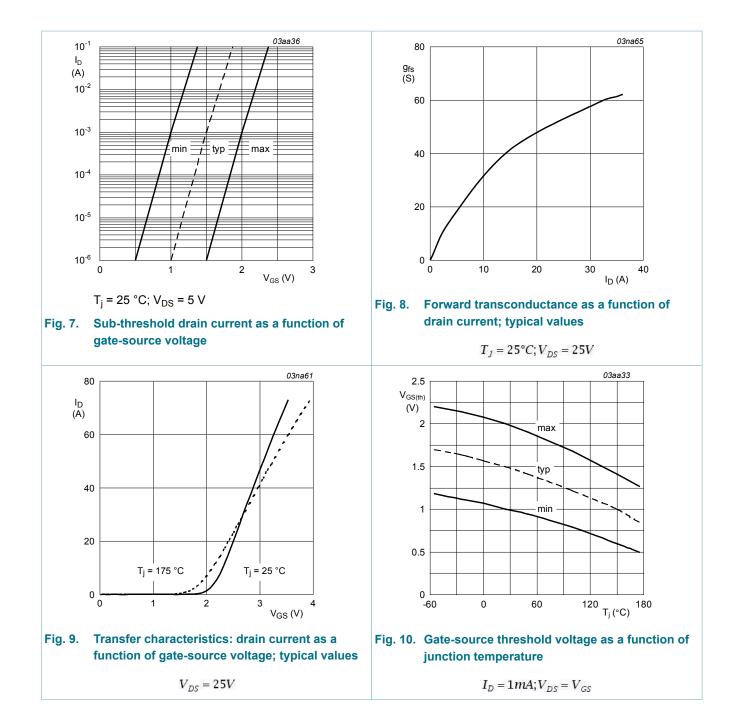


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

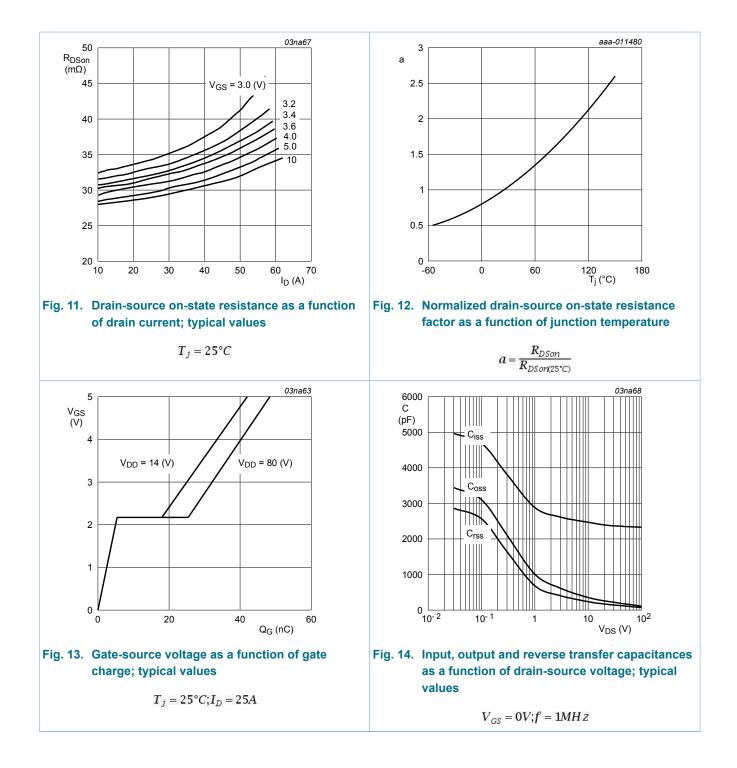
$T_i =$	$= 25^{\circ}C;I_D$	= 25A
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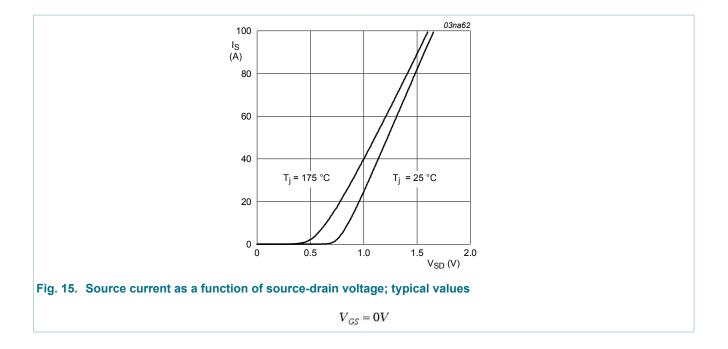


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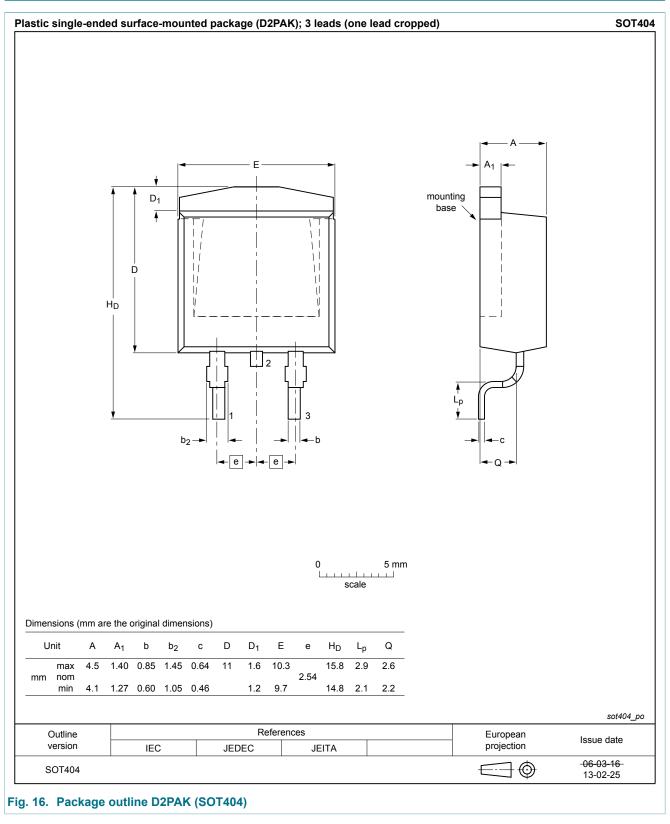
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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